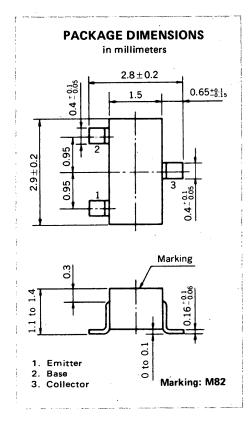
DATA SHEET

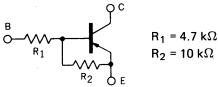


MEDIUM SPEED SWITCHING RESISTOR BUILT-IN TYPE PNP TRANSISTOR MINI MOLD



FEATURES

• Resistors Built-in TYPE



Complementary to FA1L3N

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25$	°C)		
Collector to Base Voltage	V _{CBO}	60	V
Collector to Emitter Voltage	V _{CEO}	50	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-100	mA
Collector Current (Pulse)	۱ _C	-200	mA
Maximum Power Dissipation		· ·	
Total Power Dissipation			
at 25 °C Ambient Temperature	Ρ _T	200	mW
Maximum Temperatures			
Junction Temperature	Tj	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

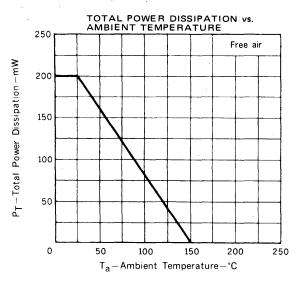
ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

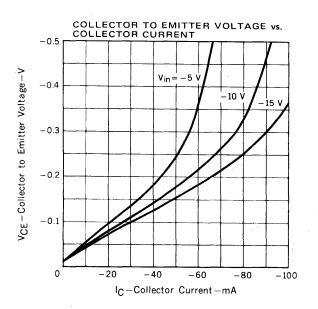
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	ІСВО			-100	nA	V _{CB} = -50 V, I _E = 0
DC Current Gain	hFE1*	35	60	100		V _{CE} = -5.0 V, I _C = -5.0 mA
DC Current Gain	^h FE2 [*]	80	200			V _{CE} = -5.0 V, 1 _C = -50 mA
Collector Saturation Voltage	V _{CE(sat)} *		-0.04	-0.2	v	I _C = -5.0 mA, I _B = -0.25 mA
Low-Level Input Voltage	VIL*		-0.9	-0.6	v	$V_{CE} = -5.0 V, I_{C} = -100 \mu A$
High-Level Input Voltage	VIH*	-3.0	-1.5		v	V _{CE} = -0.2 V, I _C = -5.0 mA
Input Resistor	R ₁	3.29	4.70	6.11	kΩ	
E-B Resistor	R ₂	7	10	13	kΩ	
Turn-on Time	t _{on}			0.2	μs	$V_{CC} = -5 V, V_{in} = -5 V$ $R_{L} = 1 k\Omega$ $PW = 2 \mu_{s}, Duty Cycle \le 2 \%$
Storage Time	t _{stg}			5.0	μs	
Turn-off Time	toff			6.0	μs	

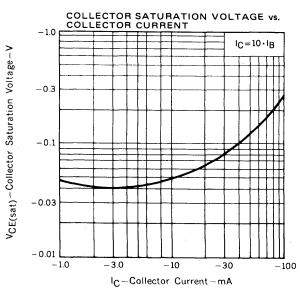
* Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

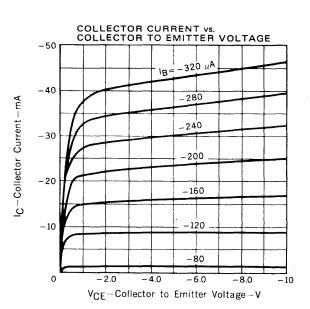
NEC cannot assume any responsibility for any circuits shown or represent that they are free from patent infringement.

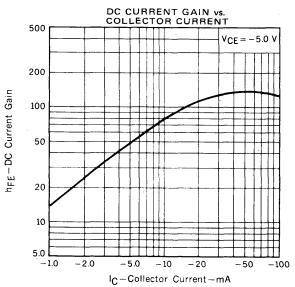
TYPICAL CHARACTERISTICS ($T_a = 25$ °C)

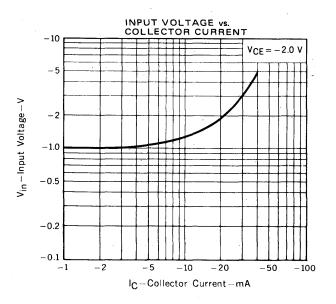


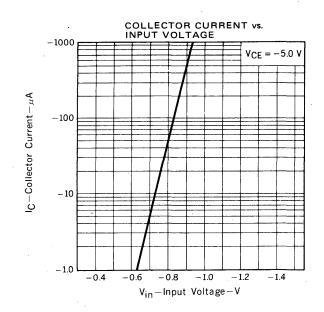


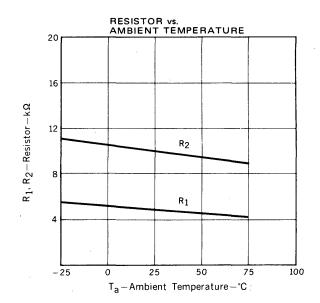












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